## **PART OBSOLETE - EOL18**

Bulletin I2717 rev. G 05/02

# International Rectifier

## **4GBU Series**

## 4.0 Amps Single Phase Full Wave

## **Bridge Rectifier**

#### **Features**

- Diode chips are glass passivated
- Suitable for Universal hole mounting
- Easy to assemble & install on P.C.B.
- High Surge Current Capability
- High Isolation between terminals and molded case (1500 V<sub>RMS</sub>)
- Lead free terminals solderable as per MIL-STD-750 Method 2026
- Terminals suitable for high temperature soldering at 260°C for 8-10 secs
- UL E160375 approved

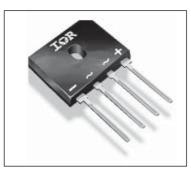
## $I_{O(AV)} = 4A$ $V_{RRM} = 50/800V$

#### Description

These GBU Series of Single Phase Bridges consist of four glass passivated silicon junction connected as a Full Wave Bridge. These four junctions are encapsulated by plastic molding technique. These Bridges are mainly used in Switch Mode power supply and in industrial and consumer equipment.

#### **Major Ratings and Characteristics**

Parameters		4GBU	Units	
Io		4	Α	
	@T <sub>C</sub>	100	°C	
I <sub>FSM</sub>	@50Hz	150	А	
	@60Hz	158	Α	
I <sup>2</sup> t	@50Hz	113	A <sup>2</sup> s	
	@60Hz	104	A <sup>2</sup> s	
$V_{RRM}$	range	50 to 800	V	
T <sub>J</sub>		- 55 to 150	°C	



4GBU

### **ELECTRICAL SPECIFICATIONS**

#### Voltage Ratings

Type number	Voltage Code	$V_{RRM}$ , max repetitive peak rev. voltage $T_J = T_J max$ .	V <sub>RMS</sub> , max RMS voltage T <sub>J</sub> = T <sub>J</sub> max. V	I <sub>RRM</sub> max. @ rated V <sub>RRM</sub> Τ <sub>J</sub> = 25°C μΑ	I <sub>RRM</sub> max. @ rated V <sub>RRM</sub> Τ <sub>J</sub> = 150°C μΑ
4GBU	005	50	35	5	400
4GBUF	01	100	70	5	400
	02	200	140	5	400
	04	400	280	5	400
	06	600	420	5	400
	08	800	560	5	400

#### **Forward Conduction**

	Parameters	4GBU	Unit	Conditions	
Io	Maximum DC output current	4	Α	T <sub>C</sub> = 100°C, Resisti	ve & inductive load
		3.2		T <sub>C</sub> =100°C, Capaci	tive load
I <sub>FSM</sub>	Maximum peak, one-cycle	150		t = 10ms	
	non-repetitive surge current,				
	following any rated load condition	158		t = 8.3ms	T <sub>J</sub> =150°C
	and with rated V <sub>RRM</sub> reapplied				
I <sup>2</sup> t	Maximum I <sup>2</sup> t for fusing,	113	A <sup>2</sup> s	t = 10ms	
	initial T <sub>J</sub> =T <sub>J</sub> max	104		t = 8.3ms	
V <sub>FM</sub>	Maximum peak forward voltage	1.0	V	T <sub>J</sub> =25°C, I <sub>FM</sub> =4A	
	per diode				
I <sub>RM</sub>	Typical peak reverse leakage	5	μA	T <sub>J</sub> =25°C, 100% V <sub>F</sub>	RRM
	current per diode				
V <sub>RRM</sub>	Maximum repetitive peak	50 to 800	V		
	reverse voltage range				

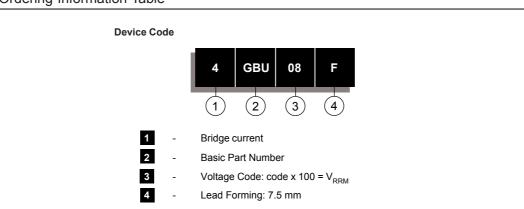
## Thermal and Mechanical Specifications

	Parameters	4GBU	Unit	Conditions
T <sub>J</sub>	Operating and storage	-55 to 150	°C	
T <sub>stg</sub>	temperature range			
R <sub>thJC</sub>	Max. thermal resistance	4.2	°C/W	DC rated current through bridge (1)
	junction to case			
R <sub>thJA</sub>	Thermal resistance,	22	°C/W	DC rated current through bridge (1)
	junction to ambient			
W	Approximateweight	4(0.14)	g(oz)	
Т	Mounting Torque	1.0	Nm	Bridge to Heatsink
		9.0	Lb.in	

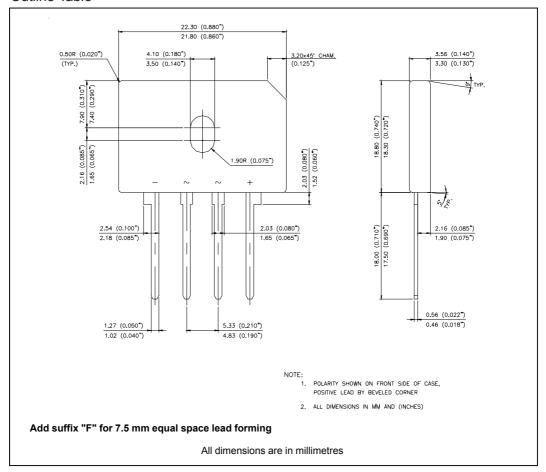
Note (1): Devices mounted on 40x40x1.5mm aluminum plate; use silicon thermal compound for maximum heat transfer and bolt down using 3mm screw

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#### Ordering Information Table



#### **Outline Table**



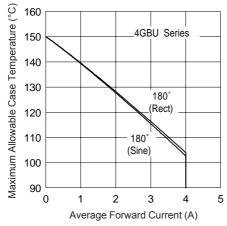


Fig. 1 - Current Ratings Characteristics

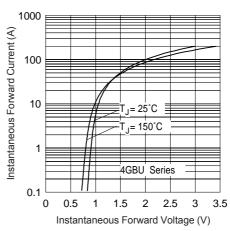


Fig. 2 - Forward Voltage Drop Characteristics

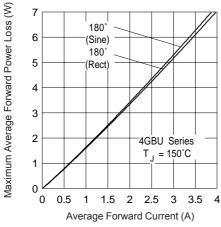


Fig. 3 - Total Power Loss Characteristics

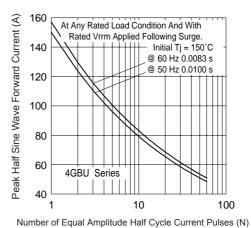


Fig. 4 - Maximum Non-Repetitive Surge Current

International **IOR** Rectifier

**4GBU Series** 

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Data and specifications subject to change without notice. This product has been designed and qualified for Multiple Level.

Qualification Standards can be found on IR's Web site.



IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7309
Visit us at www.irf.com for sales contact information. 05/02